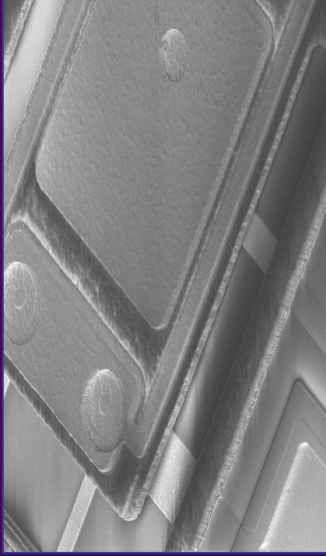
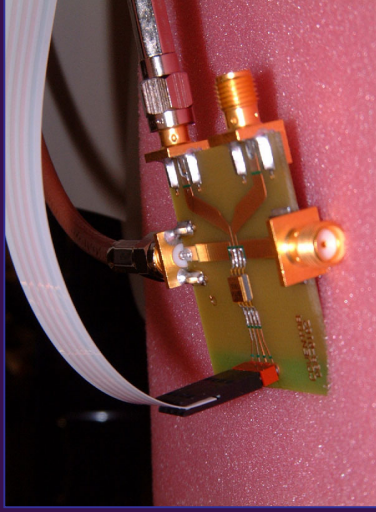
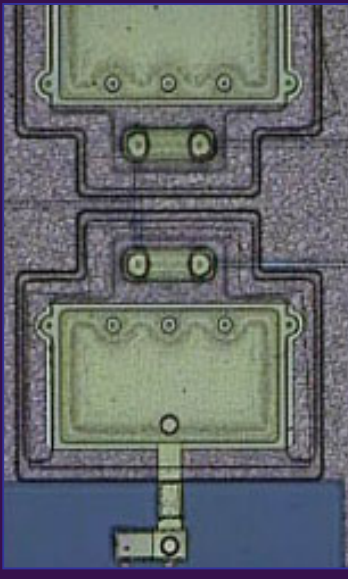


Commercial RF-MEMS: Product Opportunities and Challenges



Arthur S. Morris, III
CTO, VP Eng.



Introduction

- Who is wiSpry?
 - Spun out from Coventor at end of 2002
 - Developing RF-MEMS for services customers since 1999
 - High performance low-cost RF components
 - Broad customer evaluations underway
- Agenda
 - MEMS Technology Update
 - Promising Application Opportunities
 - Key Challenges and Solutions
 - Summary

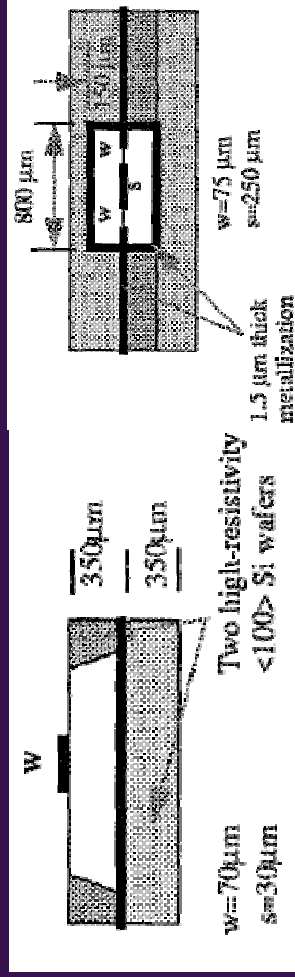


Micromachining

Transmission Lines

Maintain 50Ω at small dimensions
 With losses $< 1\text{dB/cm}$ at 10 GHz

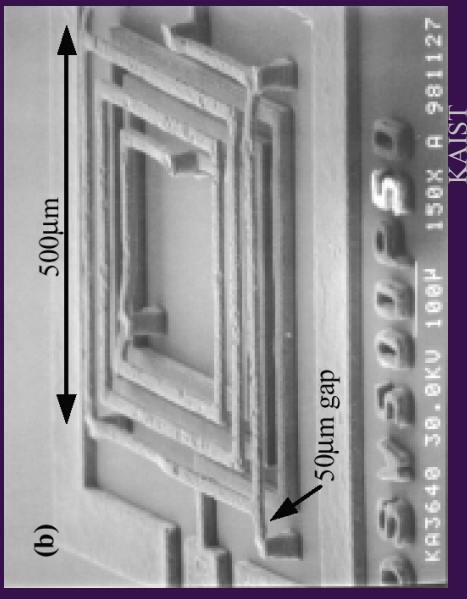
Membrane Supported Lines



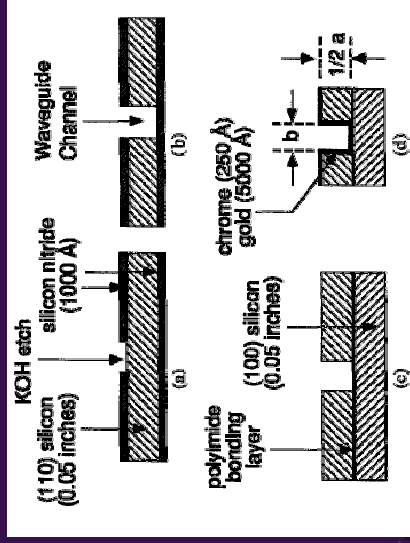
U Michigan

Inductors

$L > 14\text{ nH}$
 Q up to 100 at 2 GHz



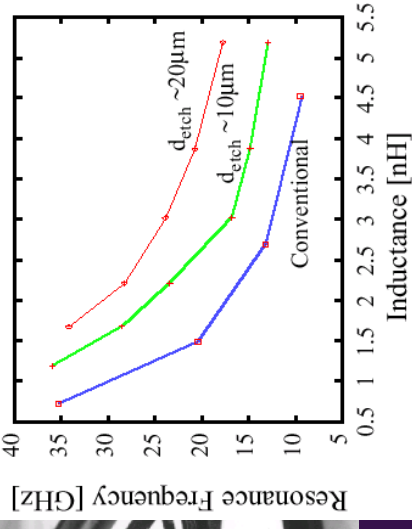
Micromachined Waveguides



JPL, CIT, IEEE

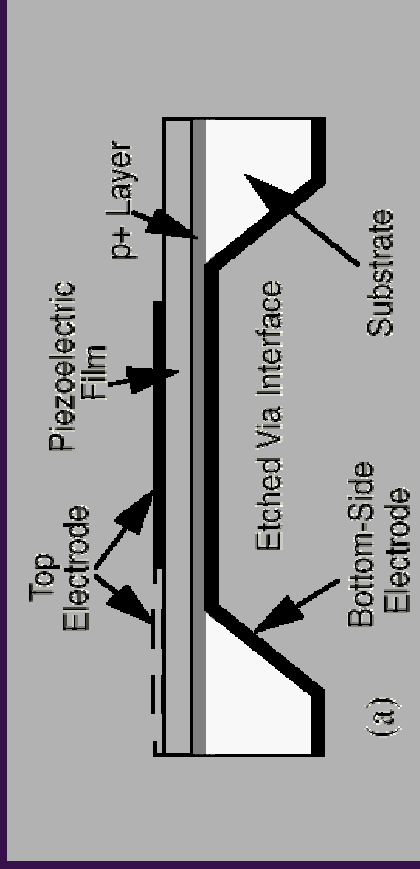
WiSpry

U Michigan



Micromechanical Resonators & Filters

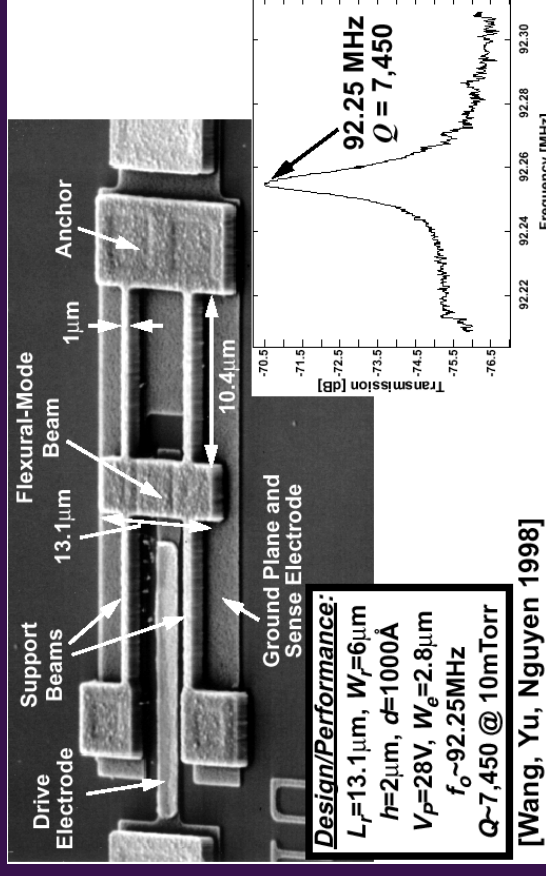
Thin-film Bulk



RF up to 7.5 GHz
 $Q > 1000$

Agilent shipping FBAR-based
SAW-replacement filters.

Flexural Mode

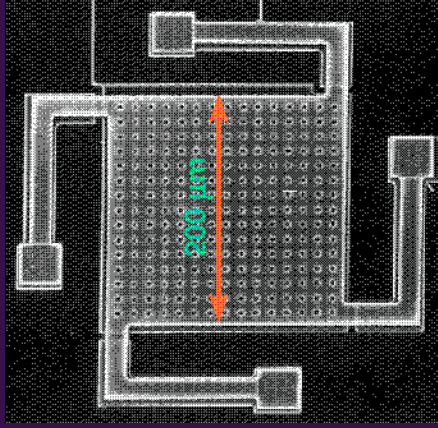


IF above 90 MHz & $Q > 7000$
Future $> 300 \text{ MHz}$ & $Q > 10000$

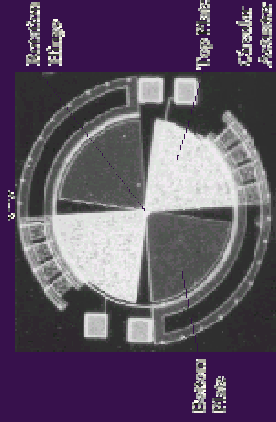
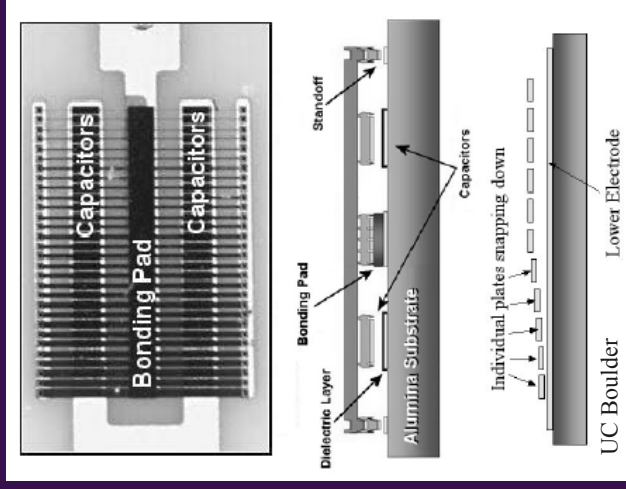
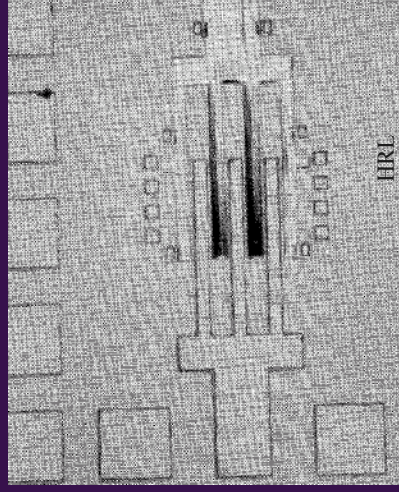
Discern sampling oscillators
stabilized with these resonators.

MEMS Varactors and Switches

Capacitance > 8 pF
 Ratios > 10:1
 Q up to 200 at 2 GHz

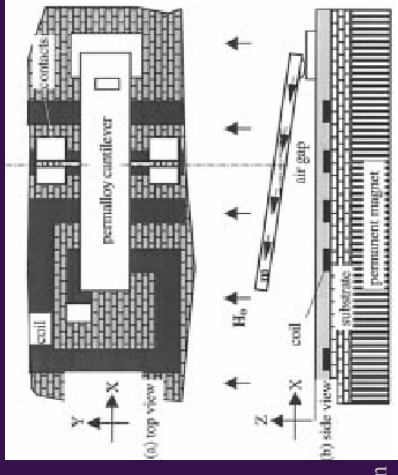
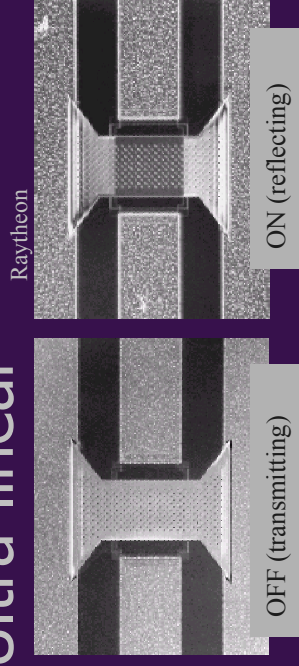


BSAC and LLNL

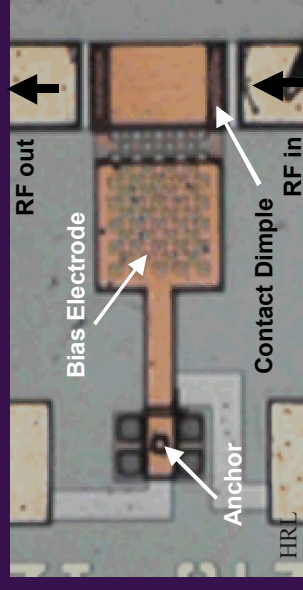


University of Hawaii

Low Loss < 0.1dB
 High Isolation > 50 dB
 Ultra-linear



Magfusion



RF-MEMS Switches

High Isolation

- Physical gap

Low Power

- Electrostatic Actuation (typ.)

Low Insertion Loss

- All metal pathway

Ultra-linear

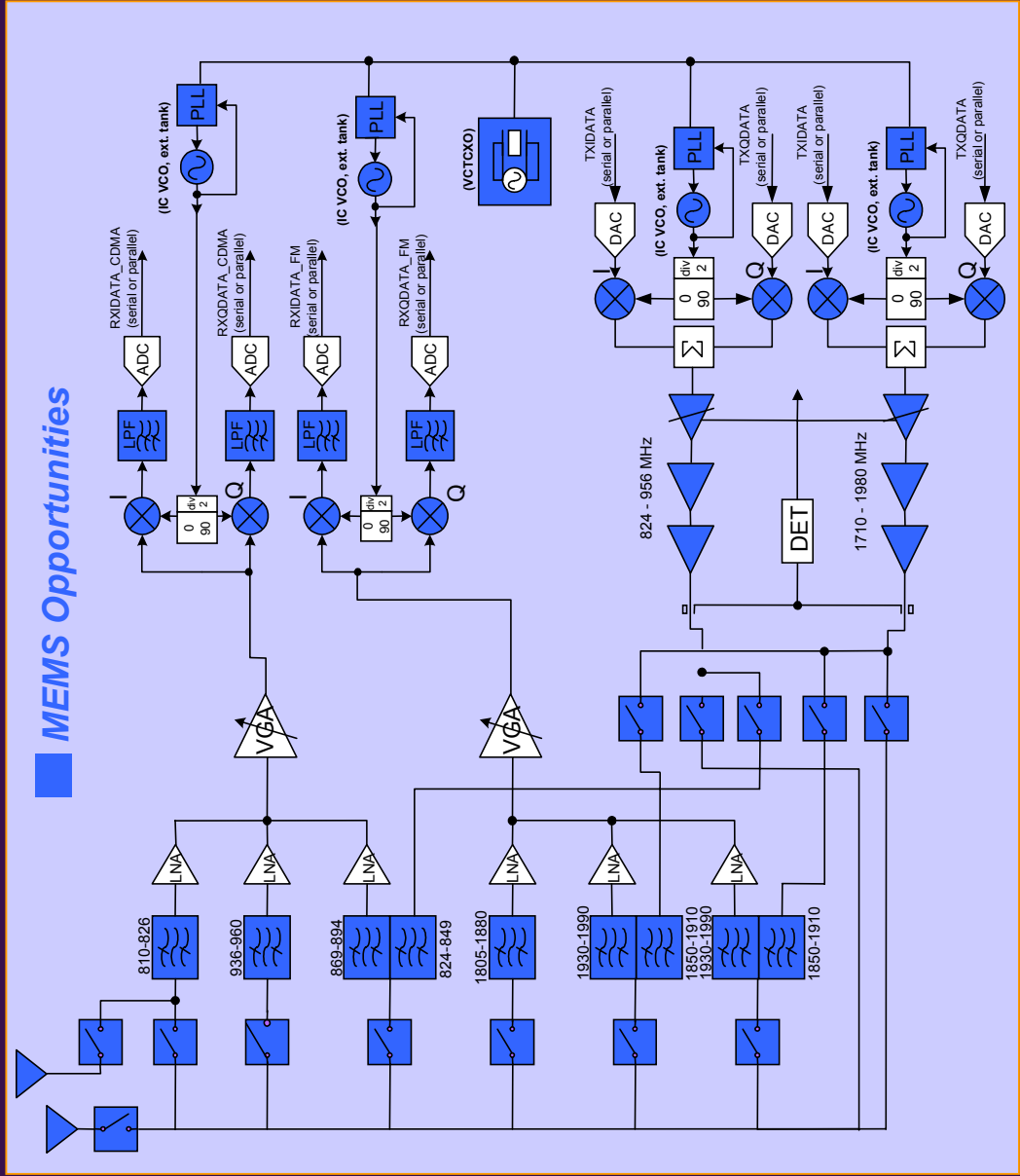
- Metal-Metal contacts

Property	MESFET		PIN Diode		PHEMT		MEMS
Series Resistance	3 Ω	5 Ω	1 Ω	3 Ω	1 Ω	3 Ω	<1 Ω
Loss at 1 GHz	0.5 dB	1.0 dB	0.5 dB	0.8 dB	0.3 dB	0.8 dB	0.1 dB
Isolation at 1 GHz	15 dB	30dB	30 dB	50 dB	20 dB	35dB	>50 dB
IP3	40-60 dBm		30-60 dBm		40-60 dBm		>70 dBm
1 dB comp.	20-35 dBm		25-40 dBm		20-40 dBm		>37 dBm ¹
Size	1-5 mm ²		2-4 mm ²		1-4 mm ²		<0.1 mm ²
Switching Speed	~ns		~ms		~ns		1-100 μ s
Control Voltage	8 V		3-5V		2.3 to 5 V		2-100V
Control Current	< 10 μ A		1 mA		< 30 μ A		<<1 μ A

MEMS Provide Low Loss, High Isolation, High Linearity and Small Size Simultaneously!

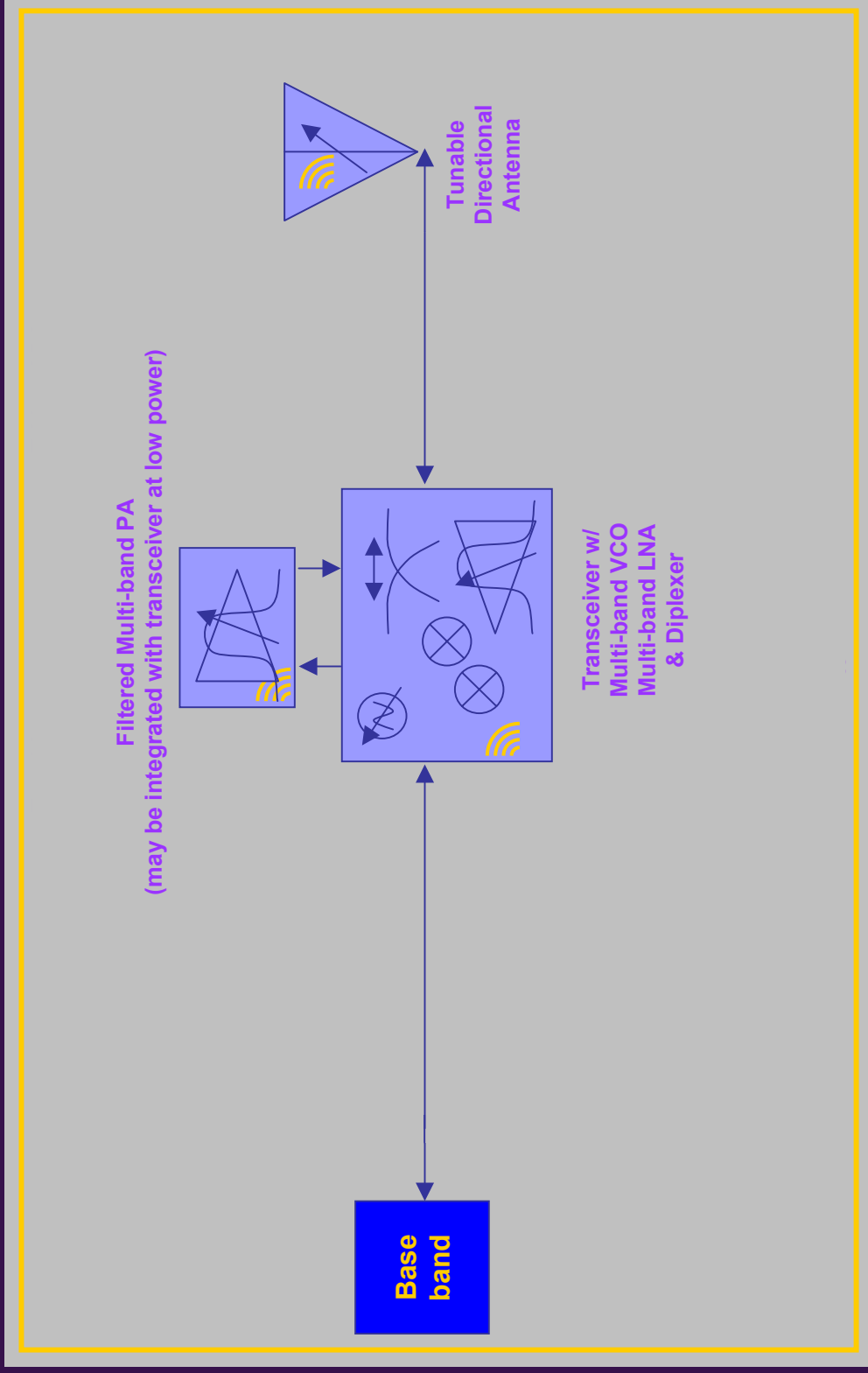
Opportunities Abound in RF Front Ends

- Reconfigurable Filters
- Tracking Filters
- Low-loss Filters
- Filter bank switching
- T/R switching
- Amp stage bypass
- Amp dynamic matching
- Amp band switching
- Antenna tuning
- Antenna reconfiguration
- Antenna phase shifters
- Tunable oscillators
- Mixers



Toward Re-configurable RF Front-Ends

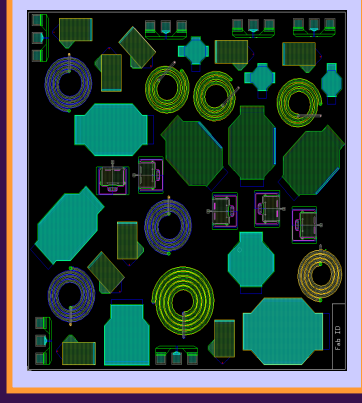
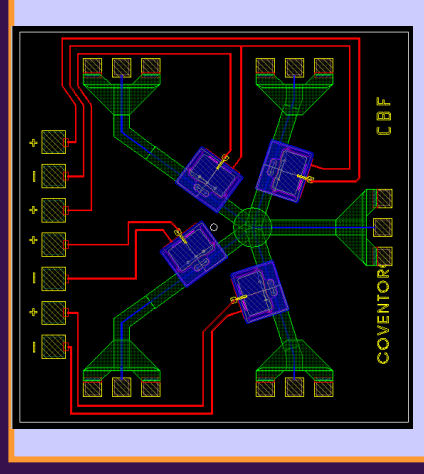
Optimal Integration of RF Architectures



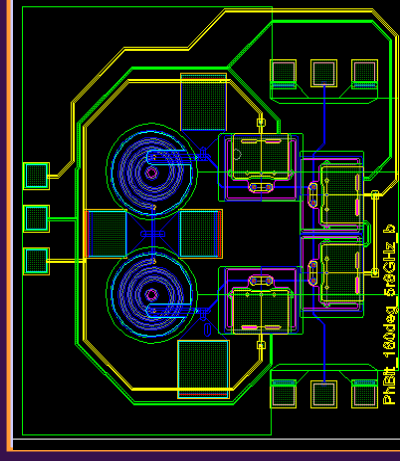
- Lower Overall Cost (Savings of 50-75% Possible)
- Smaller Footprint
- Improved RF Performance
- Faster Time to Market

WiSpry's Initial Focus

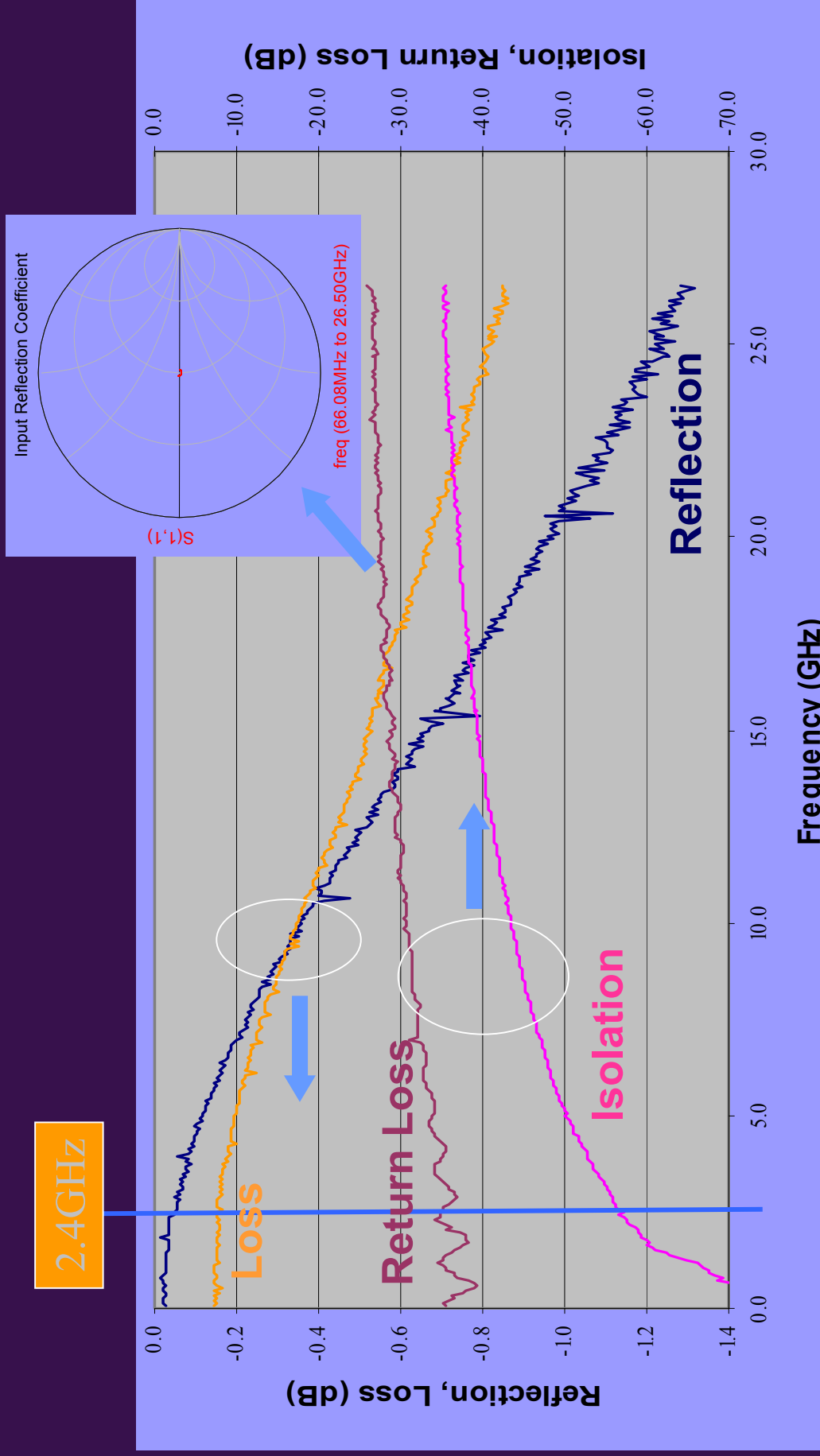
- Switches
 - Band/Mode/Path/Chain Selection
 - Beyond SP6T in $< 2 \text{ mm}^2$
 - 2-bit transfer
 - Matrices
 - High-current options
- Monolithic Switchplexer
 - Band Diplexer
 - Transmit / Receive Switching



- Phase Shifter
 - "Smart" Antennas
 - Test and measurement

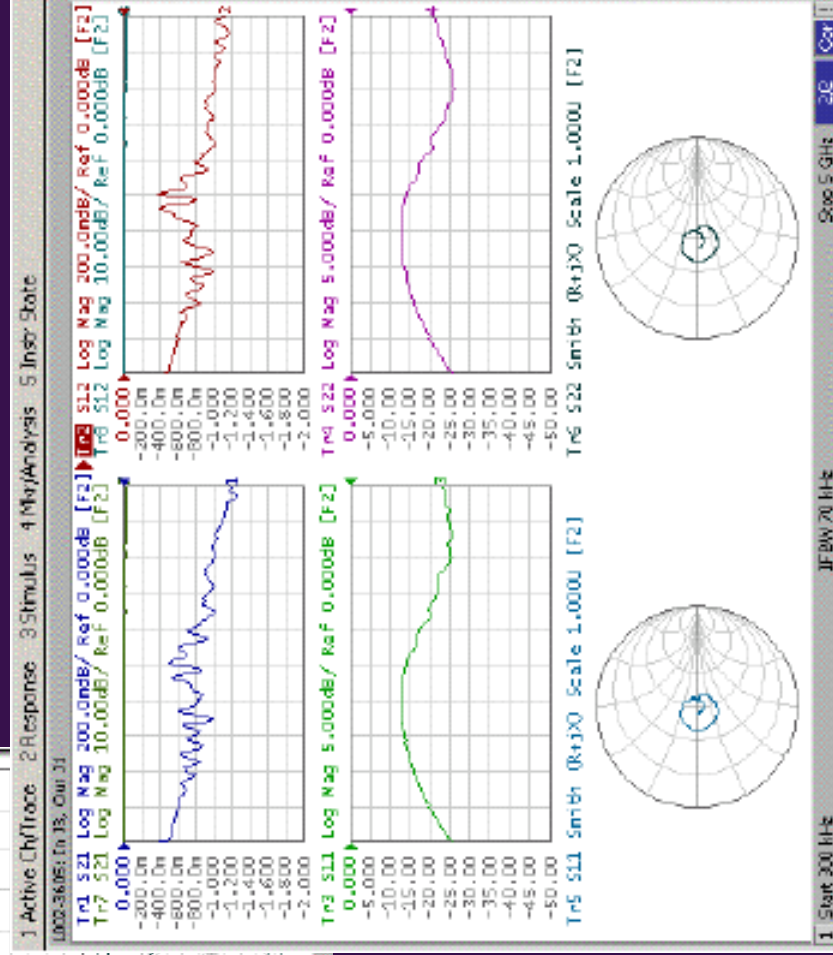
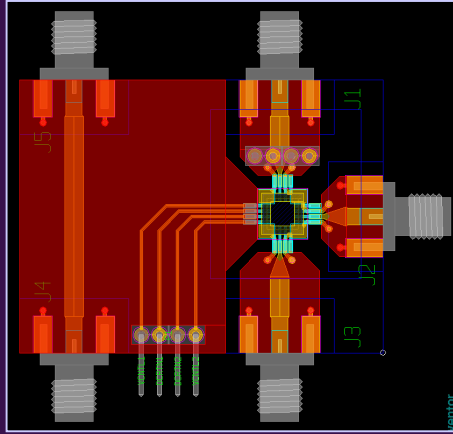
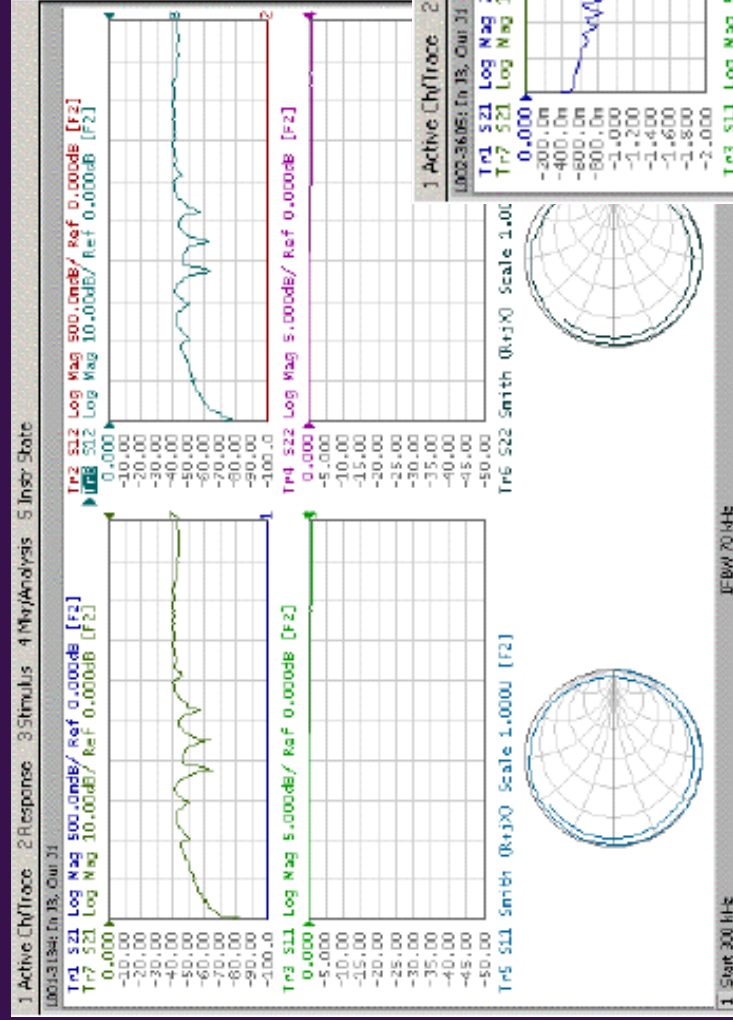
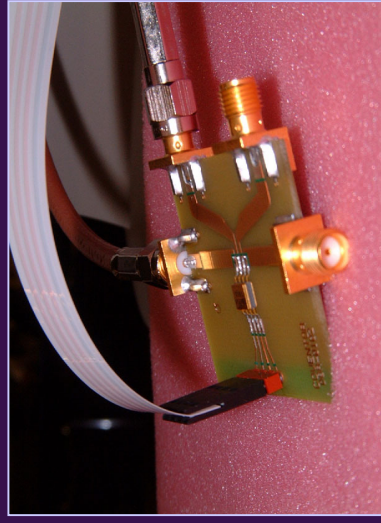


Typical Switch Die S-parameters



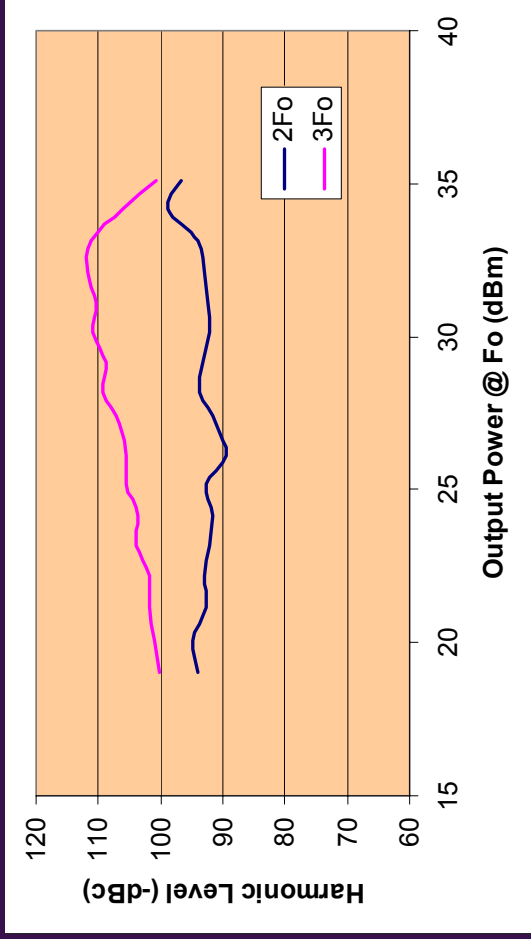
Non-deembedded results on low resistivity silicon!

Packaged S-parameters – Customer Tests

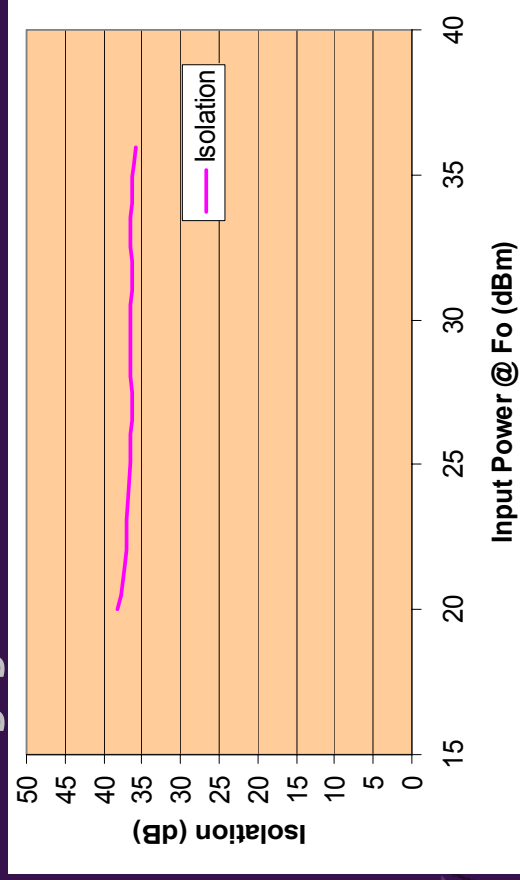


Large-Signal Switch Measurements

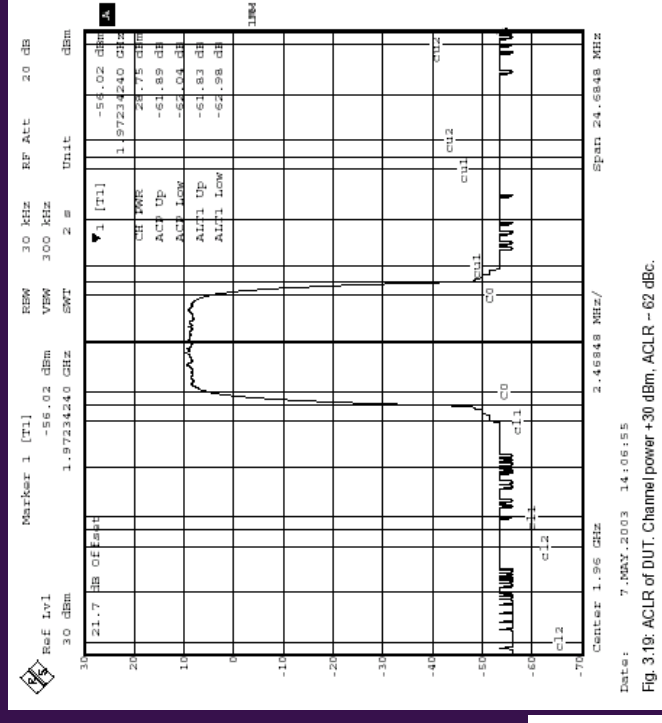
- Negligible harmonics to 4 watts



- Negligible RF actuation to 4 watts



- Clean ACLR at 1 watt



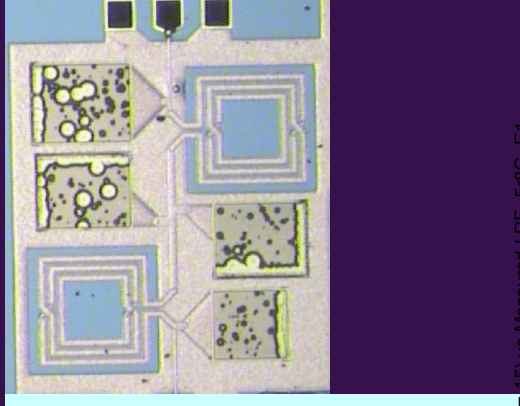
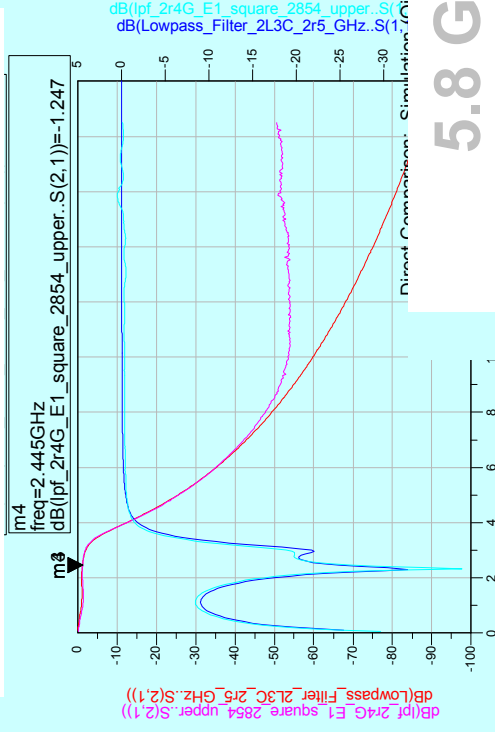
First-Pass Filter Performance

- Lowpass filters from same wafers as switches
- Sub-component of switchplexer
- Modeled design and measured data agree
- Insertion loss high
 - ◆ low resistivity substrate
 - ◆ $Q \approx 15$ @ 2.4 GHz
 - ◆ $Q \approx 12$ @ 5.8 GHz

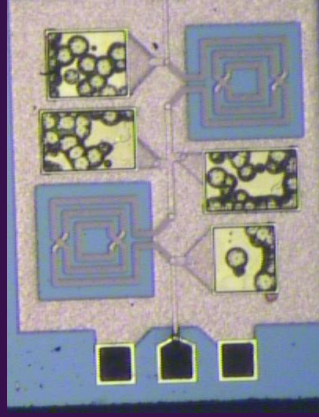
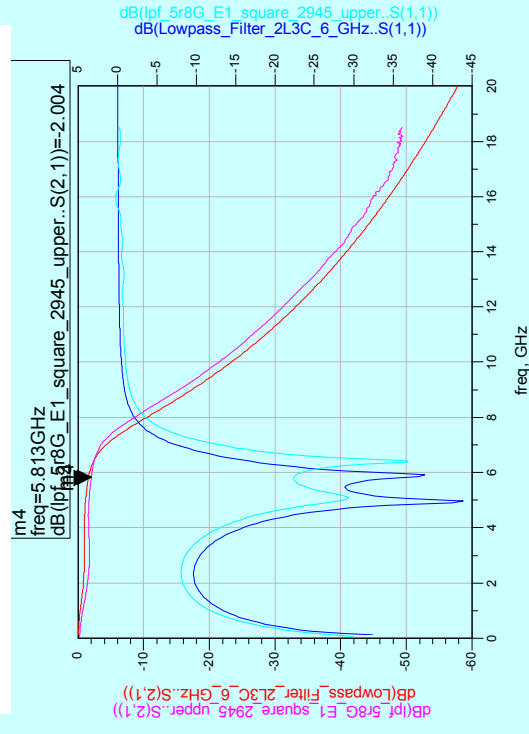
Expect $Q > 50$ with improved design

- ◆ Meet specs in next run

2.4 GHz LPF

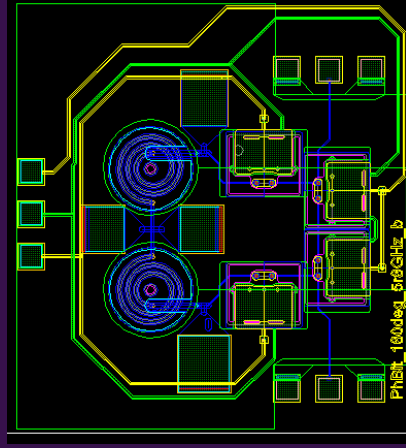


5.8 GHz LPF

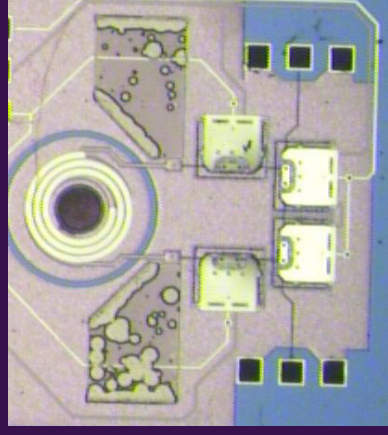


Phase Shifter

- “Smart” Antenna Applications
- Single Chip, Chip-Scale Packaged
 - $\sim 2 \text{ mm}^2$
- Through loss $< 0.2 \text{ dB}$ per bit
- Integrated Low Loss Delay Lines
 - Transmission Lines at High Frequencies
 - Compact LC Delay Line at Low Frequencies (800MHz – 6 GHz)



5.8 GHz



2.4 GHz

Key Challenges and Solutions

- Why are RF-MEMS not already in the mainstream?
 - MEMS dominate accelerometer and projection display markets
- Cost
 - Hermetic sealing and packaging
 - Size of overall solution
 - Integration barriers
 - Insufficient foundry volumes
- Reliability
 - Design/process specific issues
 - Reliability has been unproven
- Control
 - High voltages or currents have been required
 - Switching time slower than solid-state

Wafer-Level Encapsulation

Lower Cost

- Cavity packaging expensive
- Higher yield
- Lower labor costs

Easier Integration

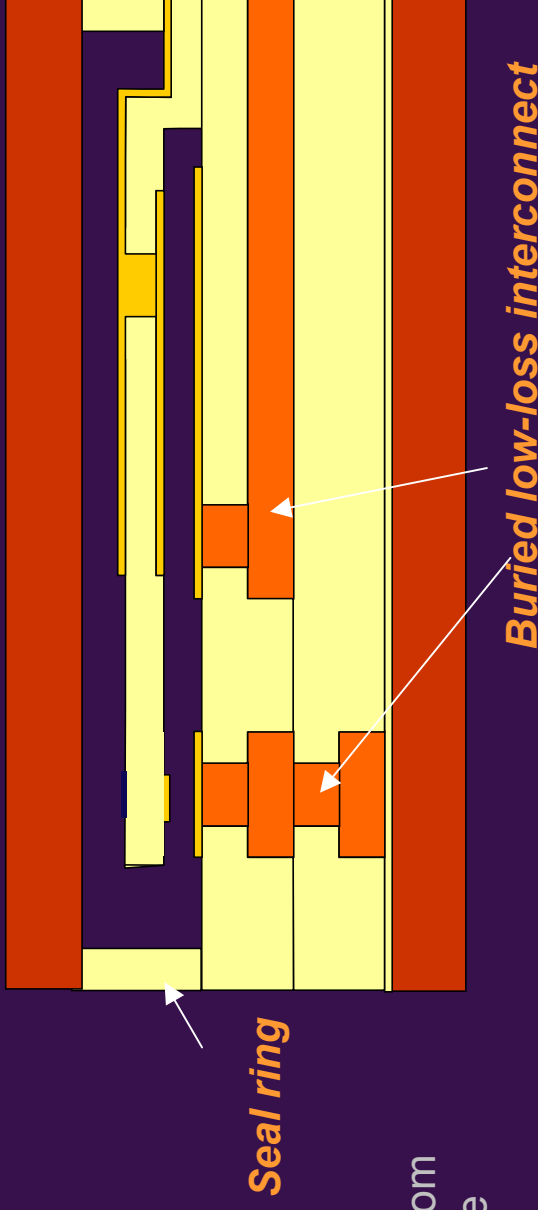
- MCM
- Flip-chip
- Monolithic

Longer Life

- Sealed in fab clean room
- Controlled atmosphere

Higher Performance

- Controlled Impedance
- Chip-on-board, etc.
- Reduced contamination



Packaging Approaches

• Protos and PCB Mounting (DRS1)

- ◆ 2 x 2 x 1.2mm package
- ◆ 400um Pitch; 200um Balls
- ◆ 25 Balls on 5 x 5 Grid

• Module Mounting (ERS1)

- ◆ 1.5 x 1.5 x 0.5mm WLCSP
- ◆ 200 um Pitch; 75um studs
- ◆ 36 pins on 6x6 grid
- ◆ Solder Ball on Plated Via
- ◆ Wafer-Level Bond

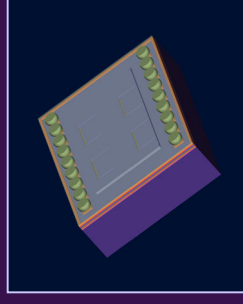
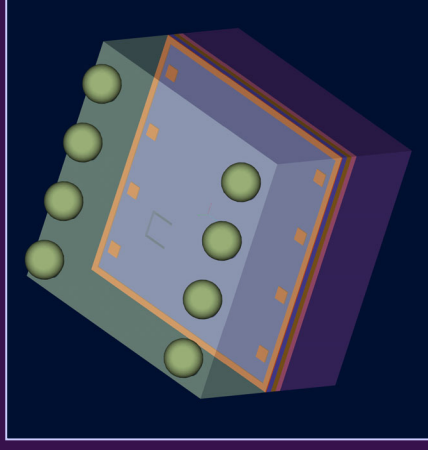
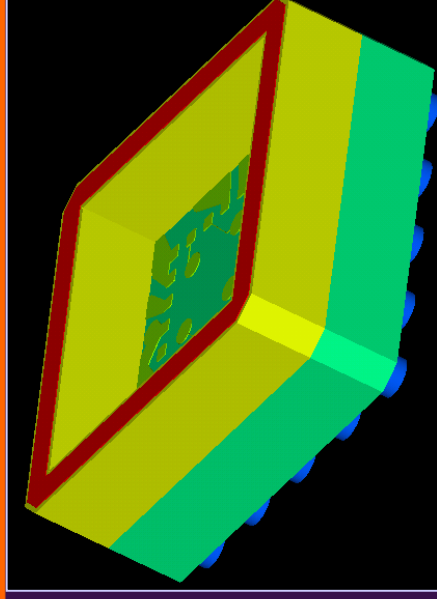
In Development



• Next-gen Module Mounting (LRS1)

- ◆ 1.0 x 1.0 x 0.3 mm WLCSP
- ◆ 150 um Pitch; 50um studs
- ◆ 32 pins; Quad Configuration
- ◆ Thin-Film Cap

In Research

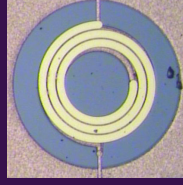
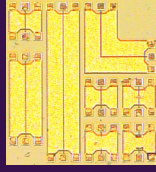


Integration within a single process

Extensive Reuse of Proven Components

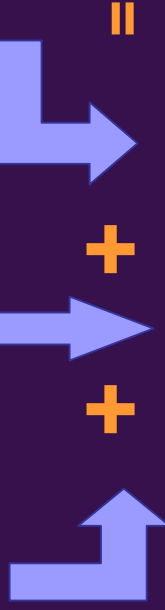
Basic Component Set

- ◆ Switches
- ◆ Transmission Lines
- ◆ Multi-layer Capacitors
- ◆ Inductors
- ◆ Transformers
- ◆ Variable Capacitors
- ◆ Variable Inductors



Post-processing of Actives

- ◆ Charge Pump Circuit
- ◆ RF-CMOS



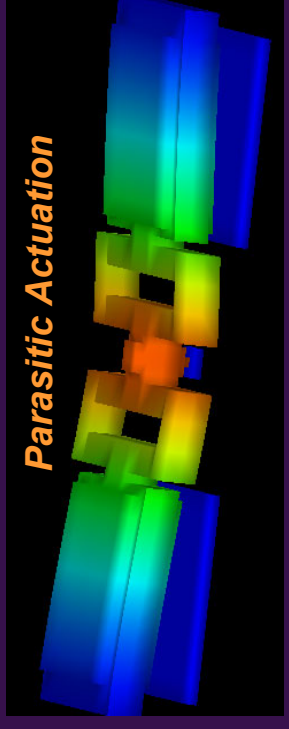
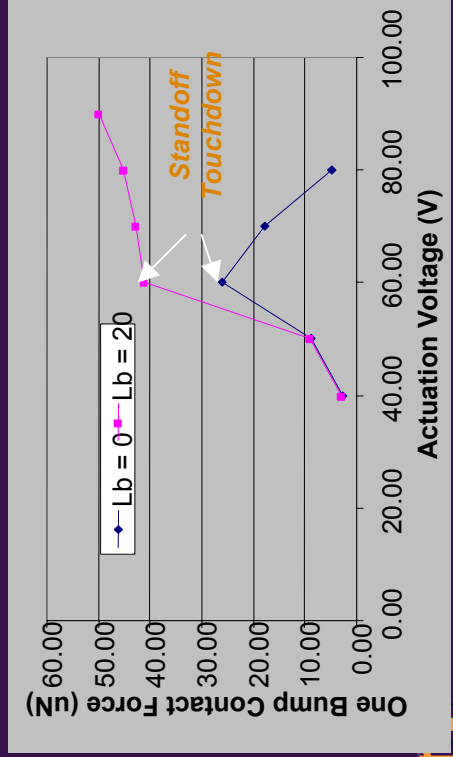
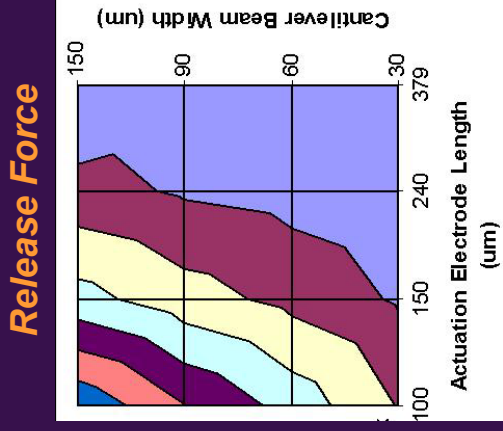
Unique RF-MEMS Process

- ◆ Low k & tanδ glass
- ◆ Thick Copper and Gold
 - No Polysilicon
- ◆ Low Thermal Budget
- ◆ Wafer-Level (Chip-Scale) Packaging
- ◆ Stand-Alone or Post-Process Any IC Wafer
 - High performance on low or high resistivity silicon
- ◆ Available in Multiple Foundries

Complete Solution

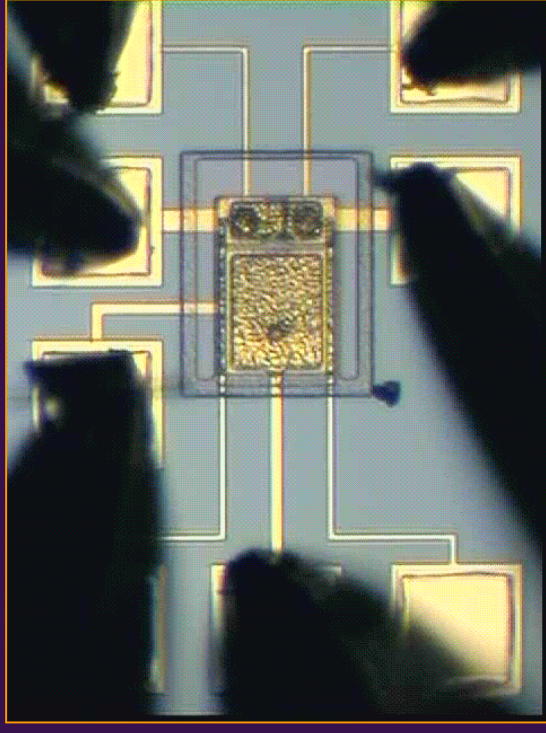
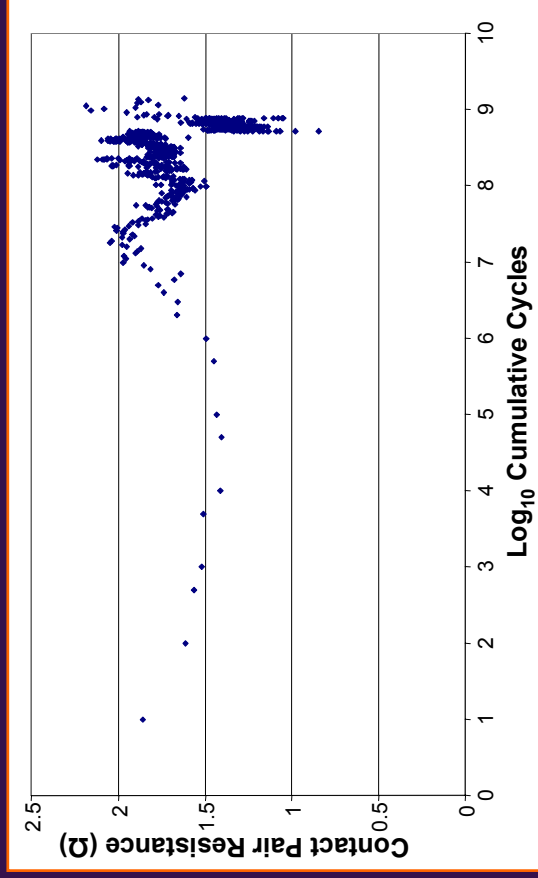
Thorough Design for Reliability

- Device Operation
 - Contact and Release Forces
 - Contact Materials
 - Electric Fields and Charging
 - Mechanical Materials
 - Mech. Stress Concentrations
 - Defect Analysis
 - Current Handling
 - Thermal Stability
 - Vibration
- Extremes
 - Overvolutaging
 - ESD
 - RF Pull-in
 - Pulsed Current
 - Shock
- Packaging
 - Sealing
 - Atmosphere
 - Gettering
 - Stresses



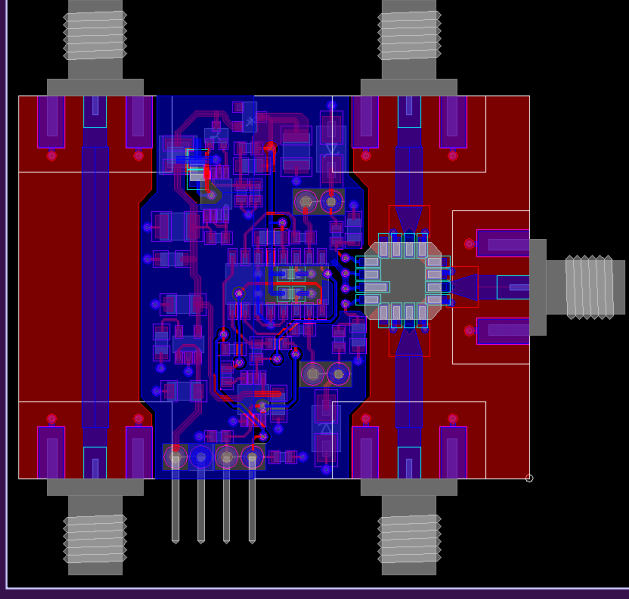
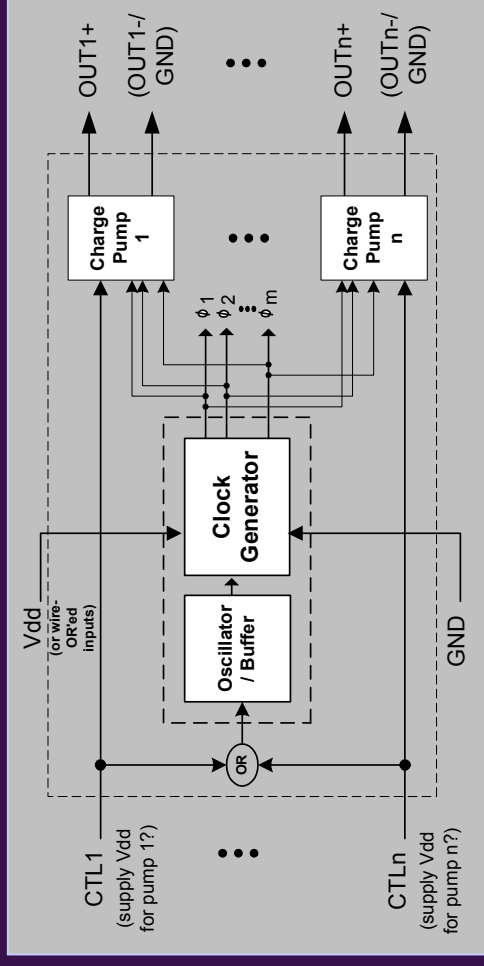
Switch Life Cycling

- Operate to billions of cycles without failure unpackaged
- Contact stable with $<1\text{ m}\Omega$ increase per million cycles
- Numerous switches tested using automated equipment
- Reliability testing of fully packaged parts is continuing
 - ◆ Acceleration method search underway



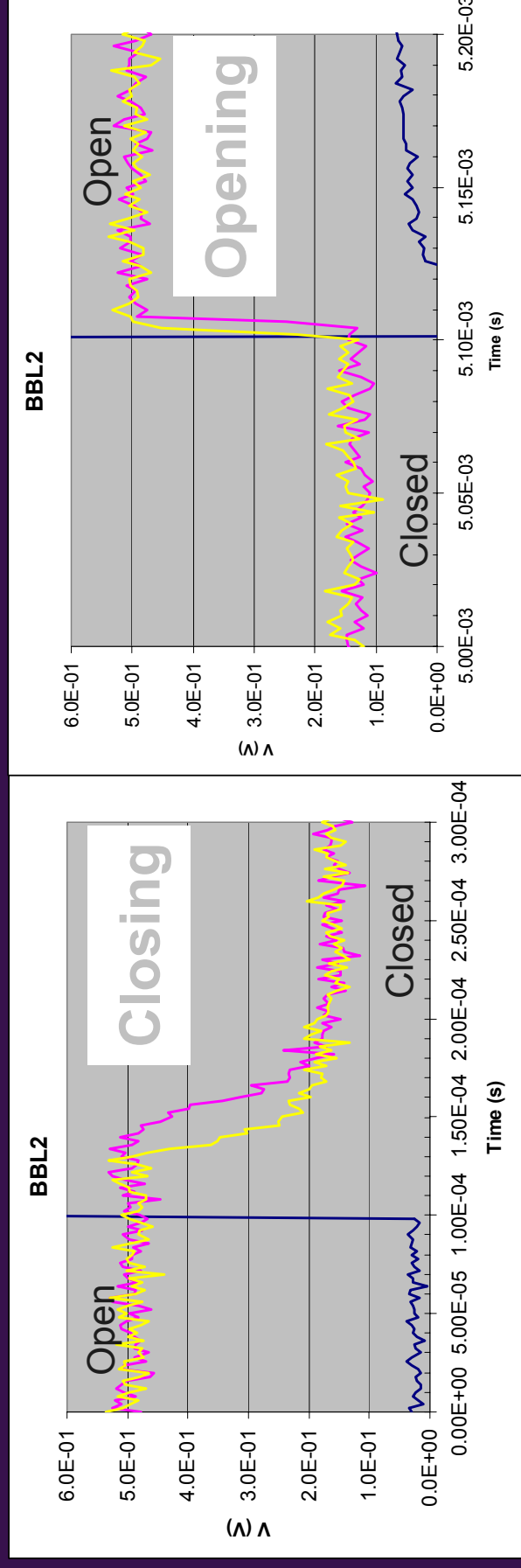
Charge Pump

- 2.7V supply
- Regulated +/- 15V Control
- Includes
 - Voltage converter
 - Switch drivers
 - CMOS/TTL Interfaces
- 35uA available per switch for worst case of continuous switching operation
- Shutdown During Stand-By
- Power Up/Down <100usec
- Discrete version built and tested
- Beginning CMOS Design



Transient Response

- Closing time: $< 100 \mu\text{s}$ to stable resistance
 - $< 50 \mu\text{s}$ delay, $< 25 \mu\text{s}$ 10%-90% RF transition
- Opening time: $< 10 \mu\text{s}$



- Fast enough for many applications, even some T/R
 - Air damping limited, easily lowered by an order of magnitude

Summary

- Low cost overall solution is key
 - ◆ Wafer-level chip-scale packaging
 - ◆ True relay -> No off-chip components required for DC-RF Isolation
 - ◆ Proprietary Unique IC Compatible Process
 - Proven; Silicon Since Late 2000; Ported and Installed in 3 Fabs
 - All Products on Same Process a la Mixed-Signal ICs; Aggregation of Volume
- High reliability achieved
 - ◆ DFM Methodology Integrated with RF IC Flow (Cadence)
 - ◆ Proven to $> 10^9$ cycles
 - ◆ Acceleration mechanisms under study
- Control issues resolved
 - ◆ Actuation Voltages are $< \pm 10V$ with Path to Lower Voltages
 - ◆ Less Demanding Charge Pump Design -> Easier direct integration
 - ◆ Speed sufficient for most commercial applications
- MEMS are ready for prime-time in RF applications
 - ◆ Proliferation of wireless standards increases need
 - ◆ Technology is maturing

Questions?

- Email: art.morris@wispry.com